

BUK9M85-60E

N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33 19 September 2016

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications 3.

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	12.8	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	31	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	68	85	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	2	-	nC



N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D I
2	S	Source		
3	S	Source		G T A
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9M85-60E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M85-60E	98560E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	60	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	31	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	12.8	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	9	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	51	Α

BUK9M85-60E

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N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode		'			
I _S	source current	T _{mb} = 25 °C		-	12.8	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	51	Α
Avalanche	ruggedness		'		'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 12.8 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	4.55	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

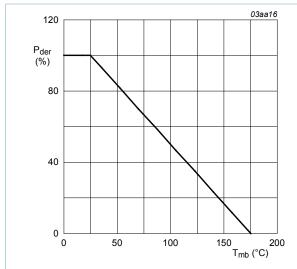


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

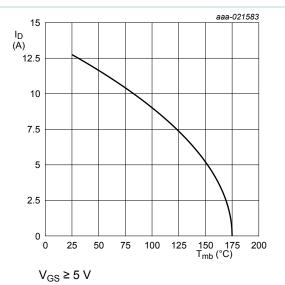
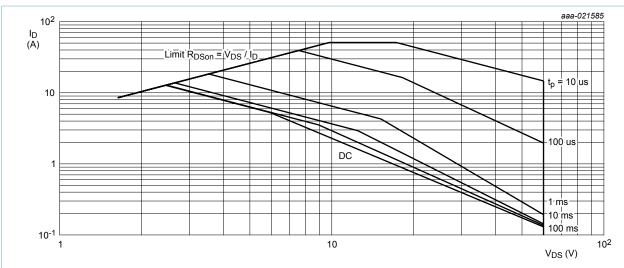


Fig. 2. Continuous drain current as a function of mounting base temperature

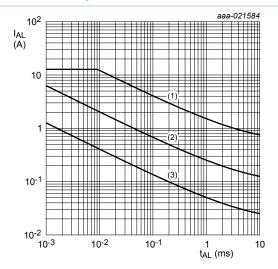
$$I_D = 12 .8A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

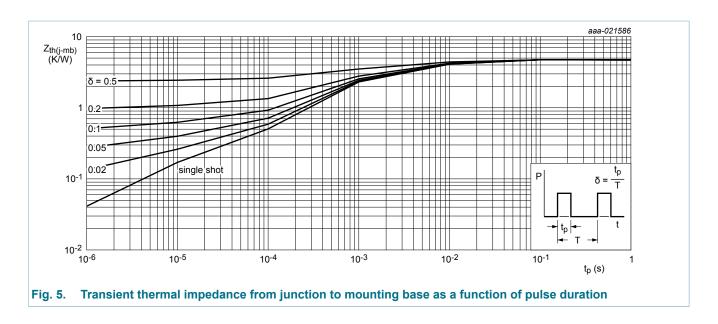
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	4.27	4.8	K/W

BUK9M85-60E

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N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					_
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS} drain	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	68	85	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	59	73	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	192	mΩ
Dynamic cl	naracteristics	,	'			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	4.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.2	-	nC
Q_{GD}	gate-drain charge		-	2	-	nC

BUK9M85-60E

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N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;		-	326	434	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	46	55	pF
C _{rss}	reverse transfer capacitance	-		-	30	41	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R_{L} = 5 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	5.4	-	ns
t _r	rise time			-	8.4	-	ns
t _{d(off)}	turn-off delay time			-	6.8	-	ns
t _f	fall time			-	5.2	-	ns
Source-dra	in diode		'	'	'		,
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; \text{ T}_j = 25 \text{ °C}$		-	24.8	-	ns
Q _r	recovered charge			-	10.8	-	nC

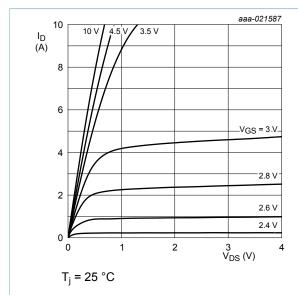


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

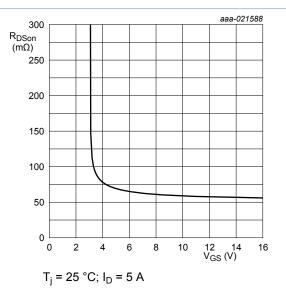


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33

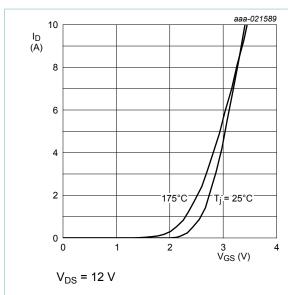


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

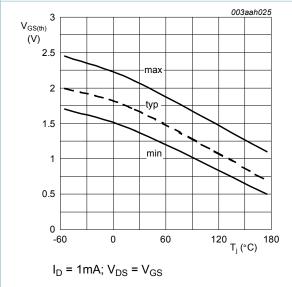


Fig. 10. Gate-source threshold voltage as a function of junction temperature

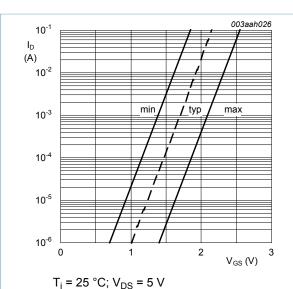


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

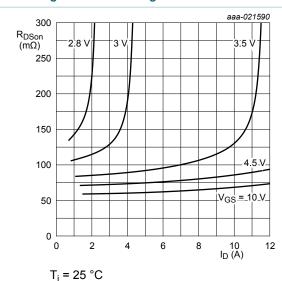


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33

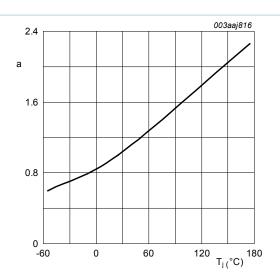


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

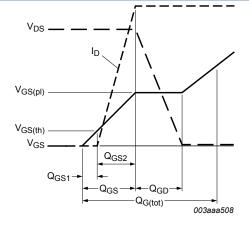


Fig. 14. Gate charge waveform definitions

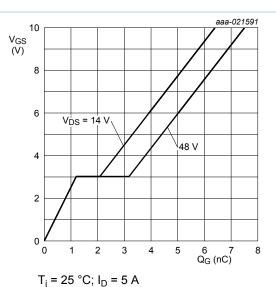
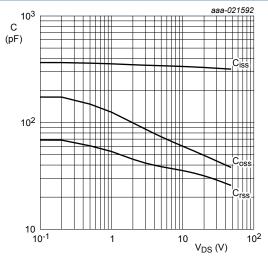


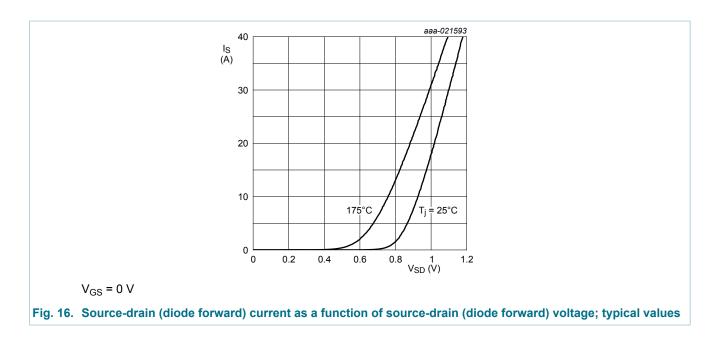
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33

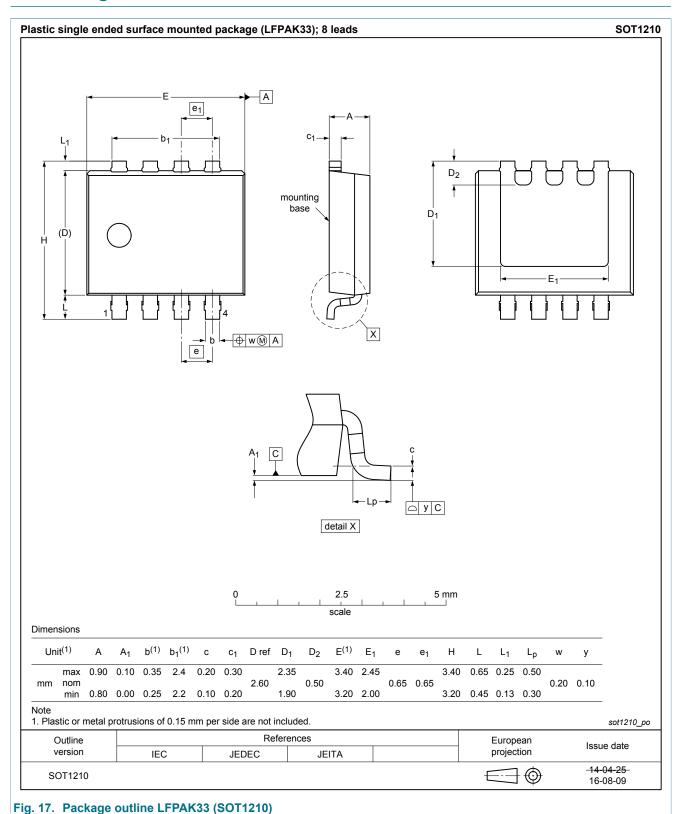


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note AN11158 "Understanding power MOSFET datasheet parameters".

N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33

12. Package outline



BUK9M85-60E

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N-channel 60 V, 85 mΩ logic level MOSFET in LFPAK33

13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel 60 V, 85 m Ω logic level MOSFET in LFPAK33

14. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	
10	Characteristics	5
11	Application information	9
12	Package outline	
13	Legal information	11
13.1	Data sheet status	11
13.2	Definitions	11
13.3	Disclaimers	11
13.4	Trademarks	12

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